

PATENT APPLICATION

Sheet 1 of 1

<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	10007804-1		
	APPLICANT		
	Kuo, et al.		
	FILING DATE	GROUP	
	Sept 4, 2003		

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
<i>SP</i>	1A	5,981,303	11/09/99	Gilton	
	1B				
	1C				
	1D				
	1E				
	1F				
	1G				
	1H				
	1I				
	1J				
	1K				

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L					
	1M					
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

<i>SP</i>	1Q	Halimaoui; Porous Silicon: Material processing, properties and applications.; Porous Silicon Science and Technology; (1994) Lecture 3
<i>SP</i>	1R	Sheng, et al.; Improved cold electron emission characteristics of electroluminescent porous silicon diodes; J. Vac. Science Technology (1997); pgs. 1661-1665
<i>SP</i>	1S	Sheng, et al.; Efficient and ballistic cold electron emission from porous polycrystalline silicon diodes with a porosity multilayer structure; J. Vac. Science Technology; (2001) pgs 64-67

EXAMINER

*Shousuegfla*

DATE CONSIDERED

*2/9/05*